



GaAs Wafer (Gallium Arsenide) Substrate MG Semiconductor materials

SUBSTRATE PROPERTY	MGGaAs3NSiPE-5000LED	MGGaAs3NSiPP-5000LED	MGGaAs3PZnPE-5000LED	MGGaAs3PZnPP-5000LED
Diameter	3 inch			
Growth Method	VGF			
Conduction Type	n-type		p-type	
Dopant	Si (Silicon)		Zn (Zinc)	
Crystal Orientation	(100)2°/6°/15° off (110)			
Carrier Concentration	(0.4~2.5)E18 cm ⁻³			
Resistivity at RT	(1.5~9)E-3 Ω·cm			
Mobility	1500-3000 cm ² /V·sec			
Etch Pit Density	<5000cm ⁻²			
Surface Finish	P/E	P/P	P/E	P/P
Thickness	220~450 um			
Applications	LED			

*The other specifications can be customized according to customer's requirements